



30V Single P-Channel Enhancement-Mode MOSFET

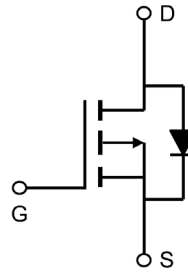
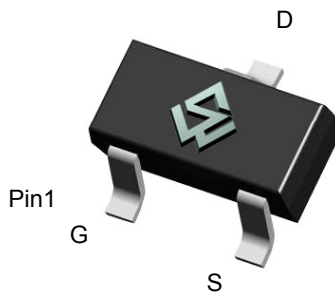
General Description

- Low gate charge.
- Use as a load switch.
- Use in PWM applications

Product Summary

- BV_{DSS} -30V
- $R_{DS(on)}$ @VGS = -10V < 60mΩ
- $R_{DS(on)}$ @VGS = -4.5V < 90mΩ

SOT-23



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current ($T_A=25^\circ\text{C}$)	I_D	-4.2	A
Drain Current ($T_A=75^\circ\text{C}$)		-2.0	A
Pulsed Drain Current ^a	I_{DM}	-20	A
Power Dissipation ^b ($T_A=25^\circ\text{C}$)	P_D	1.25	W
Power Dissipation ^b ($T_A=75^\circ\text{C}$)		0.9	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Junction-to-Ambient ^a ($t \leq 10\text{s}$)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction-to-Ambient ^{a,d} (Steady-State)		130	$^\circ\text{C/W}$
Junction-to-Lead (Steady-State)	$R_{\theta JL}$	90	$^\circ\text{C/W}$

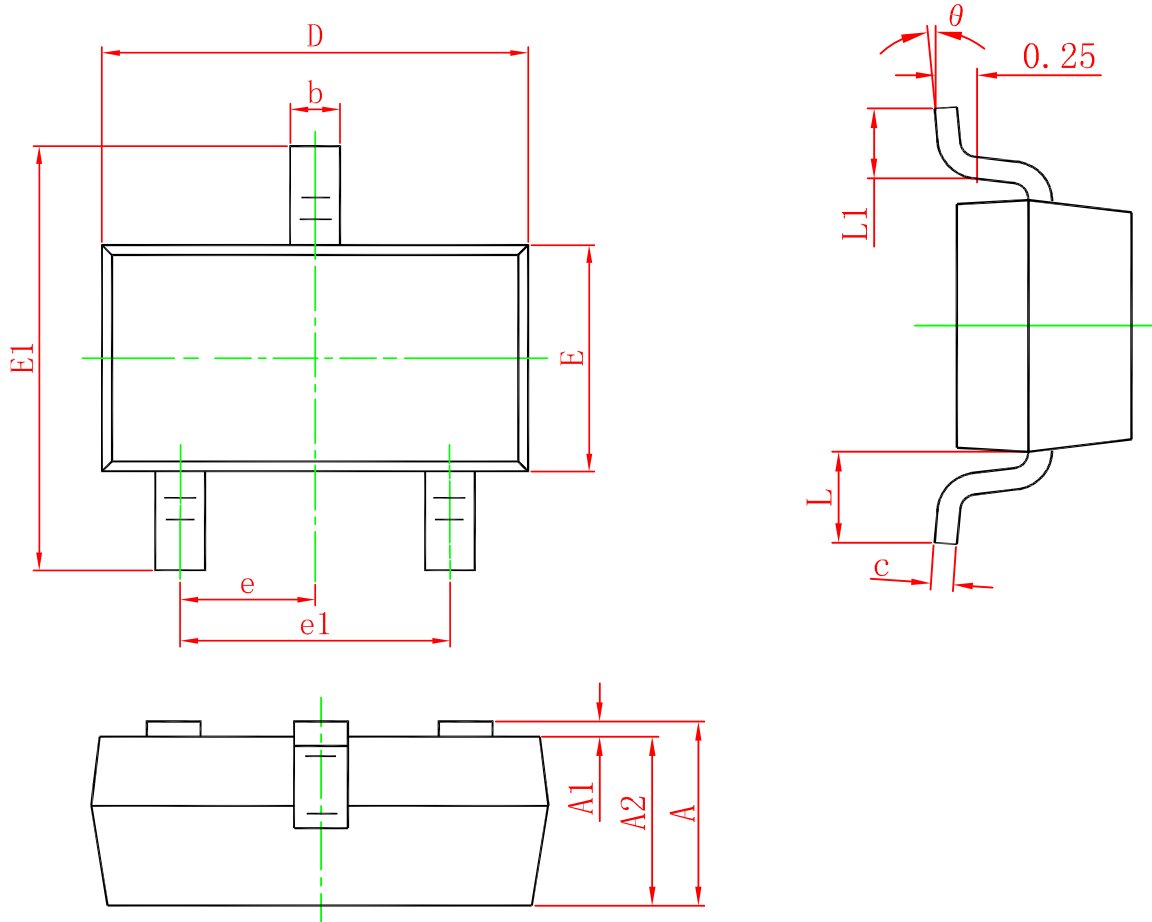


Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1		-3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -4.2A$			60	$\text{m}\Omega$
		$V_{GS} = -4.5V, I_D = -2.0A$			90	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = -10V, I_D = -4.2A$		15		S
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -1.0A$			-1.2	V
I_S	Maximum Body-Diode Continuous Current				-2.0	A
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V$ $f = 1.0\text{MHz}$		550		pF
C_{oss}	Output Capacitance			110		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
Switching Characteristics						
Q_g	Total Gate Charge	$V_{DS} = -15V, I_D = -4.2A$ $V_{GS} = -6V$		11		nC
Q_{gs}	Gate-Source Charge			2.2		nC
Q_{gd}	Gate-Drain Charge			3.5		nC
$t_{D(ON)}$	Turn-On Delay Time	$V_{DD} = -15V, I_D = -1A$ $V_{GS} = -6V$ $R_{GEN} = -6\text{ohm}$		8		ns
t_r	Turn-On Rise Time			6.2		ns
$t_{D(OFF)}$	Turn-Off Delay Time			23		ns
t_f	Turn-Off Fall Time			8		ns

- Repetitive rating, Pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$
- The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.
- The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design.
- The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.



SOT-23 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.	0.022 REF.		
θ	0.300	0.500	0.012	0.020

单击下面可查看定价，库存，交付和生命周期等信息

[>>SiliconWisdom\(矽睿半导体\)](#)